

Inventor: Gurtej S. Sandhu et al.

Title: Methods of Forming A Thin Film Transistor

Assignee: Micron Technology, Inc.



INFORMATION DISCLOSURE STATEMENT

PURSUANT TO 37 C.F.R. §§ 1.56, 1.97 AND 1.98

In compliance with 37 C.F.R. §§ 1.56, 1.97 and 1.98, your attention is directed to the United States patents and other references listed on the attached Form PTO-1449. No admission is made regarding whether all the submitted references are prior art.

The listed references were cited by, or submitted to, the Office in the parent, co-pending application of the above-identified application. The above-identified application is a divisional application of co-pending application Serial No. 09/837,645, filed April 17, 2001. Such prior disclosure is sufficient for the above-identified application as far as copies of the references are concerned. 37 C.F.R. § 1.98(d) and MPEP § 609(2).

Citation of these references is respectfully requested.

Respectfully submitted,

Dated: July 21, 2004

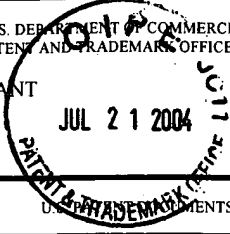
By: Jennifer J. Taylor
Jennifer J. Taylor, Ph.D.
Reg. No. 48,711

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Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE <div style="border: 2px solid black; border-radius: 50%; padding: 10px; display: inline-block; transform: rotate(-15deg);"> RECEIVED JUL 21 2004 PATENT & TRADEMARK OFFICE </div>			ATTY. DOCKET NO. MI22-1780		SERIAL NO. 09/902,277	
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)								
APPLICANT Gurtej S. Sandhu et al.					FILING DATE July 9, 2001			
					GROUP 2813			
U.S. PATENT DOCUMENTS								
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
	AA	5,320,975	6/1994	Cederbaum et al.	437	44		
	AB	5,334,861	8/1994	Pfiester et al.	257	67		
	AC	5,373,170	12/1994	Pfiester et al.	257	69		
	AD	5,411,909	5/1995	Manning et al.	437	52		
	AE	5,418,393	5,1995	Hayden	257	347		
	AF	4,945,065	7/31/90	Gregory, et al.	437	4		
	AG	5,212,108	5/18/93	Liu, et al.	437	60		
	AH	5,523,240	6/4/96	Zhang, et al.	437	21		
	AI	5,726,096	3/98	Jung	438	592		
	AJ	4,569,697	7/86	Tsu et al.				
	AK	5,665,611	9/97	Sandhu et al.	438	162		
FOREIGN PATENT DOCUMENTS								
		Document Number	Date	Country	Class	Subclass	Translation	
							Yes No	
	AL	281054A1	7/90	Germany - Mende, et al.				
	AM							
	AP							
OTHER PRIOR ART (including Author, Title, Date, Pertinent Pages, Etc.)								
	AR		Pollack, G.P. et al., "Hydrogen Passivation of Polysilicon MOSFET's From A Plasma Nitride Source", IEEE, 1984 pp. 408-410					
	AS		Kamins, T.I., "Hydrogenation of Transistors Fabricated in Polycrystalline-Silicon Films", IEEE, 1980, pp. 159-161					
	AT		Seager, C.H. et al., "Studies of the hydrogen passivation of silicon grain boundaries", J.Appl. Phys. 52, February 1981, pp. 1050-1055					
EXAMINER				DATE CONSIDERED				
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.								

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Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. M122-1780		PRIORITY SERIAL NO. 09/837,645	
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT Gurtej S. Sandhu et al.			
				PRIORITY FILING DATE April 17, 2001		PRIORITY GROUP 2813	



*Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
	AA	5,605,848	2/97	Ngaoaram		
	AB	5,364,803	11/94	Lur et al.		
	AC	5,830,802	11/98	Tseng et al.	438	592
	AD	5,372,860	12/94	Fehlner et al.	427	578
	AE	5,552,332	9/96	Tseng et al.		
	AF	5,753,543	5/19/98	Sandhu et al.	438	163
	AG	6,001,675	12/14/99	Sandhu et al.	438	151
	AH	6,077,732	6/20/00	Sandhu et al.	438	158
	AI	6,238,957	5/29/01	Sandhu et al.	438	151
	AJ					
	AK					

FOREIGN PATENT DOCUMENTS							
Document Number	Date	Country	Class	Subclass	Translation		
					Yes	No	
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AM							
AN							
AO							
AP							

OTHER PRIOR ART (including Author, Title, Date, Pertinent Pages, Etc.)			
AR		Kitajima, H. et al., "Leakage Current Reduction in Sub-Micron Channel Poly-Si TFTs", Extended Abstract - 1991 International Conference on Solid State Devices and Materials, Yokohama, 1991, pp. 174-176	
AS		Sunada, Takeshi et al., "The Role of Fluorine Termination in the Chemical Stability of HF-Treated Si Surfaces", Dept. of Electrical Engineering, Hiroshima University, Higashi-Hiroshima 724, Accepted for Publication 1990	

EXAMINER	DATE CONSIDERED
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